

T-33-07

2SD325

2010A

NPN/PNP Triple Diffused Planar
Silicon Transistors**2SB511**

Low Frequency Power Amp Applications

©398F

. 5 Watts AF Power amplifier output use. There are complementary pair.

():2SB511

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

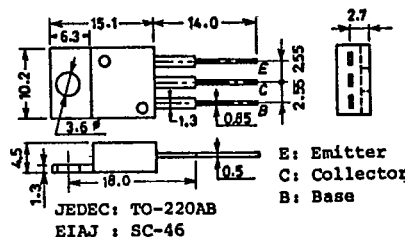
Collector to Base Voltage	V_{CB0}	(-) 35	V
Collector to Emitter Voltage	V_{CE0}	(-) 35	V
Emitter to Base Voltage	V_{EB0}	(-) 5	V
Collector Current	I_C	(-) 1.5	A
Peak Collector Current	i_{cp}	(-) 3	A
Collector Dissipation	P_C	1.75	W
		10	W
		150	$^\circ\text{C}$
Junction Temperature	T_j	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}		

 $T_c=25^\circ\text{C}$ Electrical Characteristics at $T_a=25^\circ\text{C}$

		min	typ	max	unit
Collector Cutoff Current	I_{CBO} $V_{CB}=(-)20\text{V}, I_E=0$			(-) 0.1	mA
Emitter Cutoff Current	I_{EBO} $V_{EB}=(-)4\text{V}, I_C=0$			(-) 1.0	mA
DC Current Gain	$h_{FE}(1)$ $V_{CE}=(-)2\text{V}, I_C=(-)1\text{A}$	40*		320*	
	$h_{FE}(2)$ $V_{CE}=(-)2\text{V}, I_C=(-)0.1\text{A}$	35			
Gain Bandwidth Product	f_T $V_{CE}=(-)5\text{V}, I_C=(-)0.5\text{A}$		8		MHz
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C=(-)1.5\text{A}, I_B=(-)0.15\text{A}$		(-) 1.0		V
Base to Emitter Voltage	V_{BE} $I_C=(-)1\text{A}, V_{CE}=(-)5\text{V}$		(-) 1.5		V

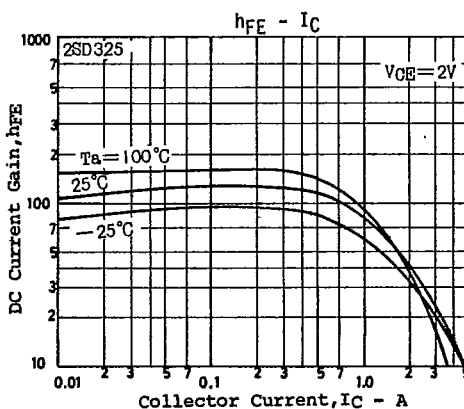
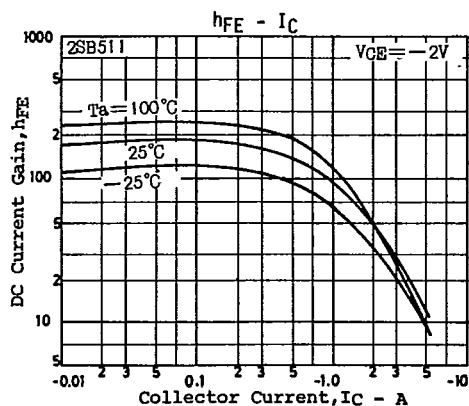
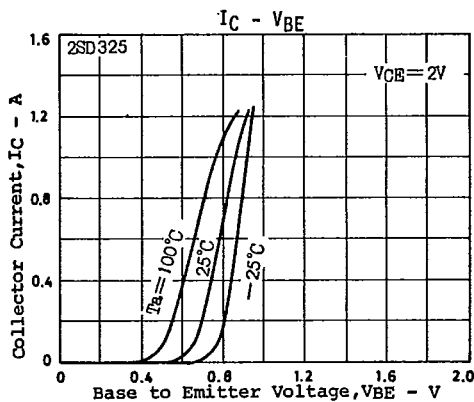
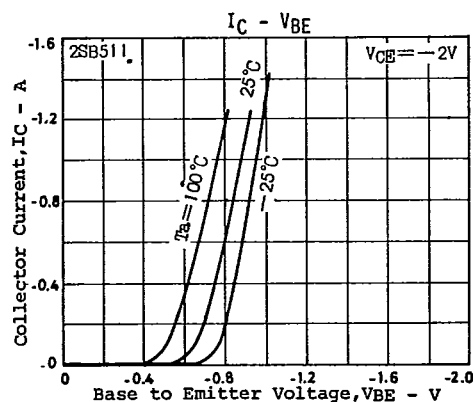
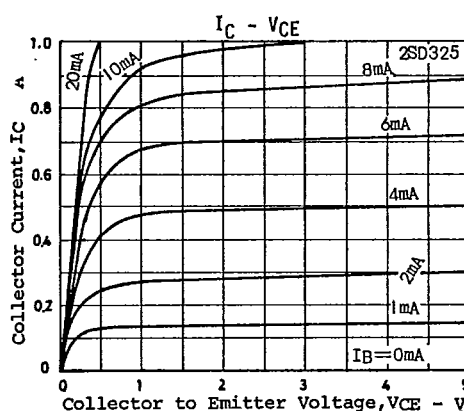
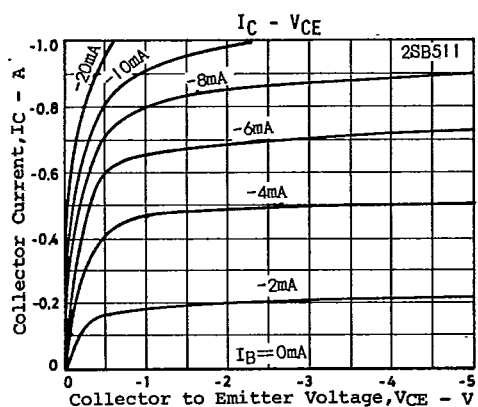
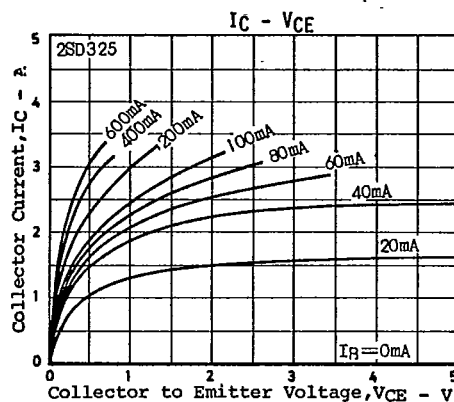
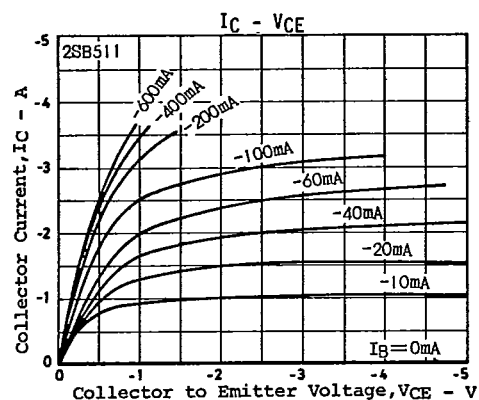
*: The 2SB511/2SD325 are classified by 1A h_{FE} as follows:

40	C	80	60	D	120	100	E	200	160	F	320
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Case Outline 2010A
(unit:mm)

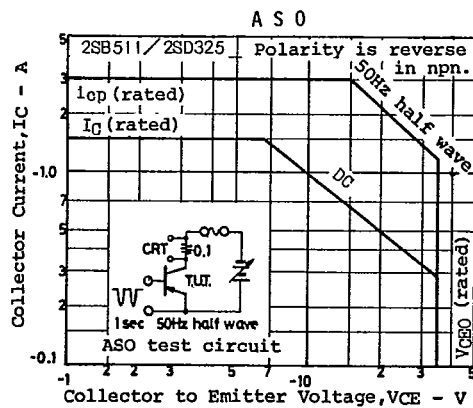
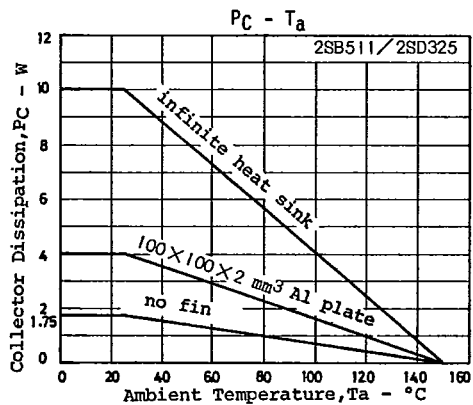
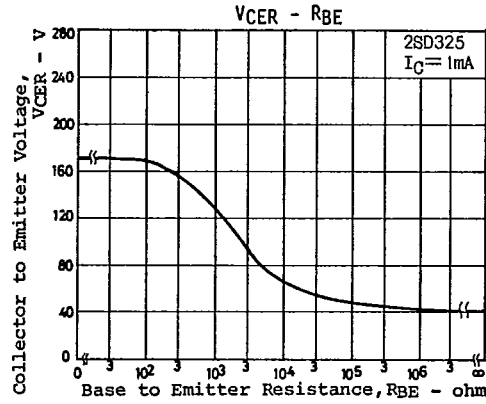
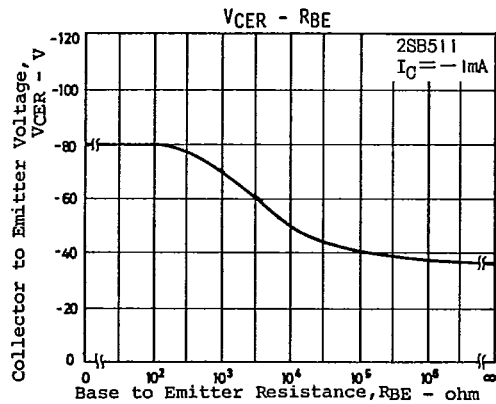
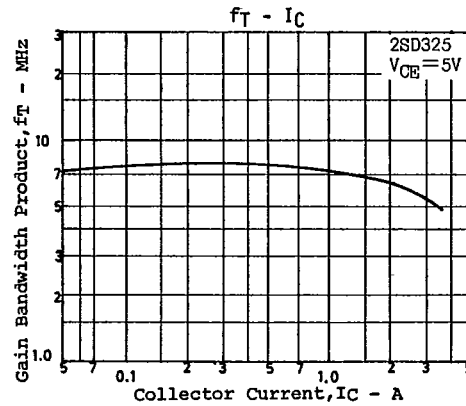
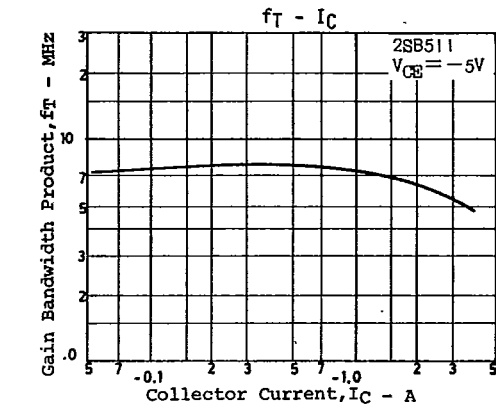
2SD325/2SB511

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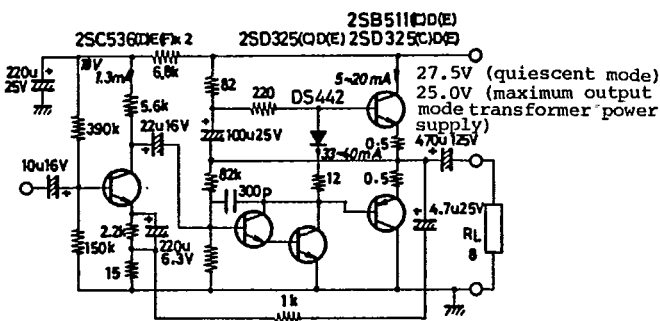


2SD325/2SB511

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Application Circuit 1: 8W Pure Complementary Push-pull Power Amp. Using 2SB511/2SD325.

If NFB is applied from after the coupling capacitor, phase shift occurs at low frequencies, increasing the gain at low frequencies as indicated by curve a in Fig. A. NFB is applied from before the output capacitor as shown right to avoid this phenomenon. However, since the voltage actually developed across the load is the voltage divided by the capacitor and load resistor, the gain starts lowering at a rather lower frequency. Therefore, the value of capacitor C_{NF} connected in series with the feedback resistor is made to be 4.7 μ F.



Main Characteristics

Voltage Gain

VG

Without NFB

65 to 67 dB

With NFB

35.8 dB

Output Power

Po

THD=5%

7.2 to 8.6 W

Total Harmonic Distortion

THD

Po+3W

0.03 to 0.09 %

Input Impedance

ri

65 to 80 kohm

Output Impedance

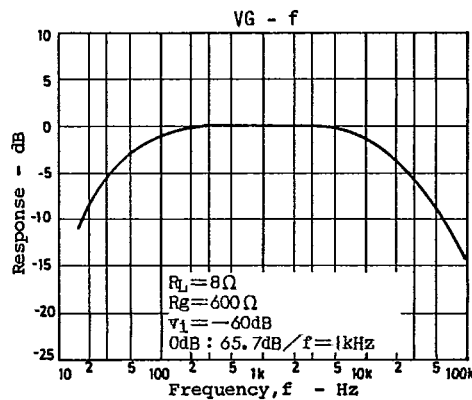
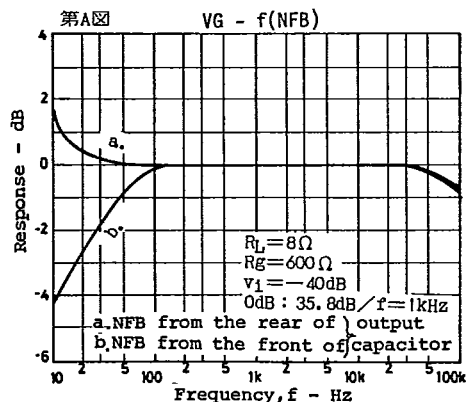
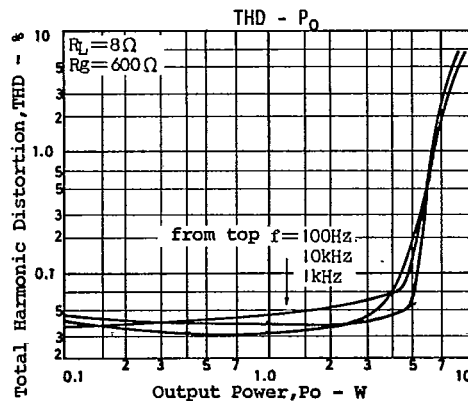
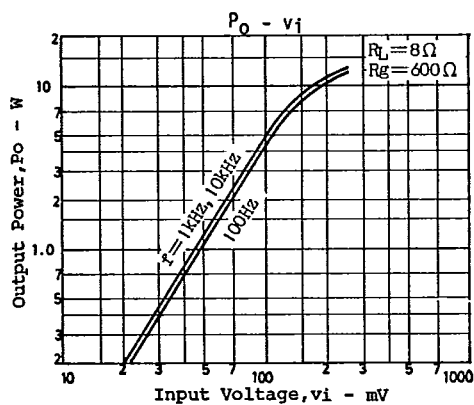
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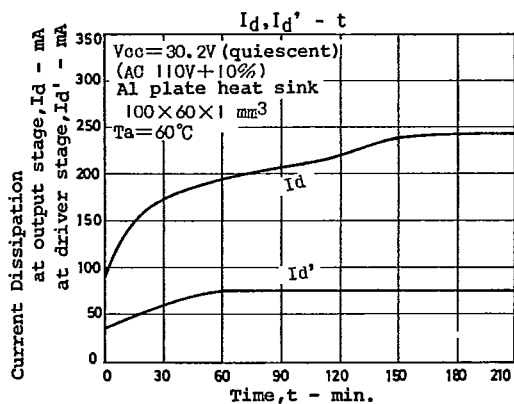
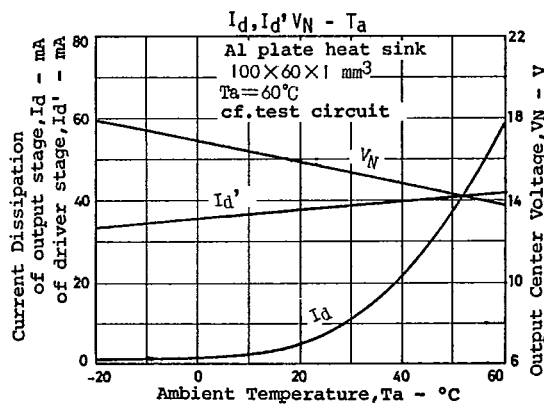
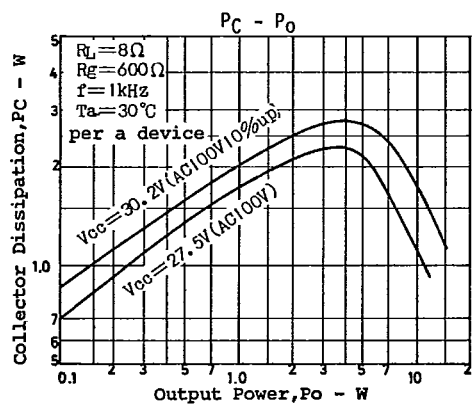
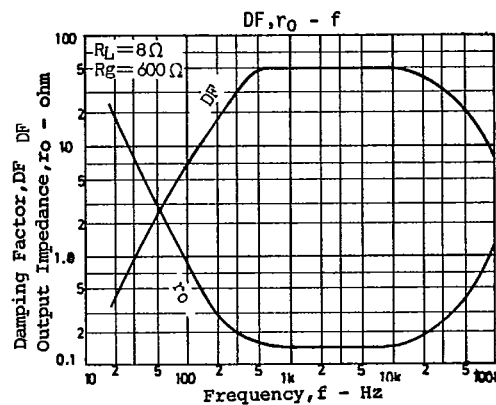
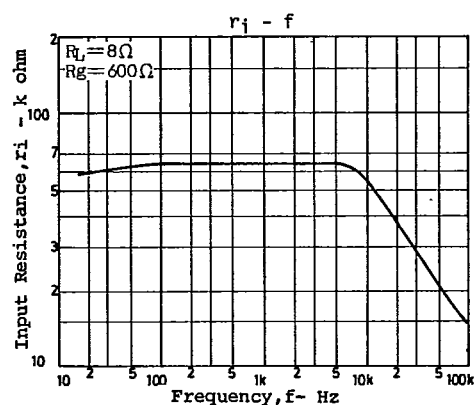
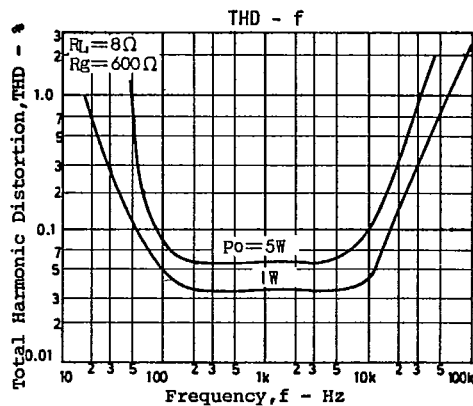
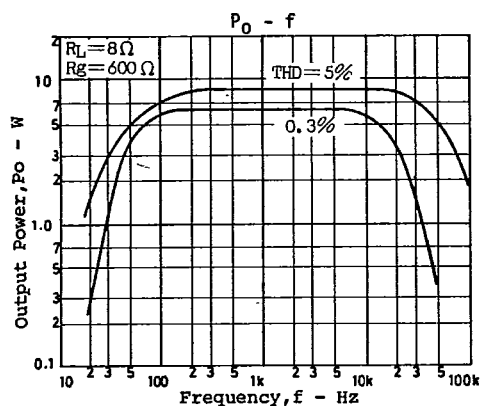
0.16 ohm

Damping factor

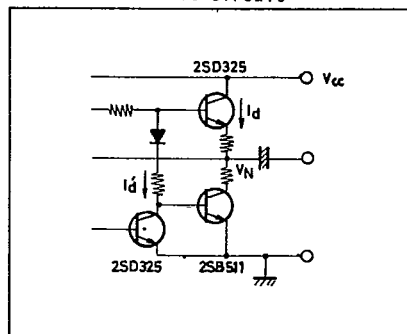
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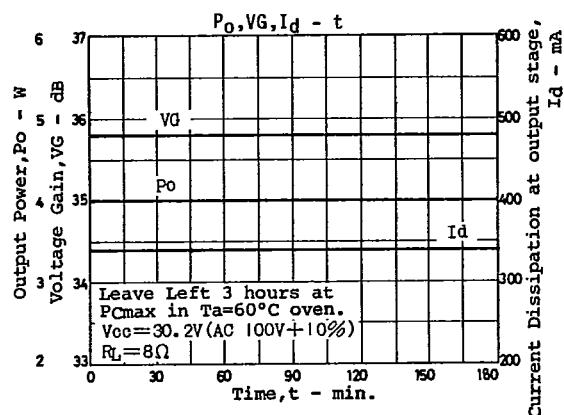
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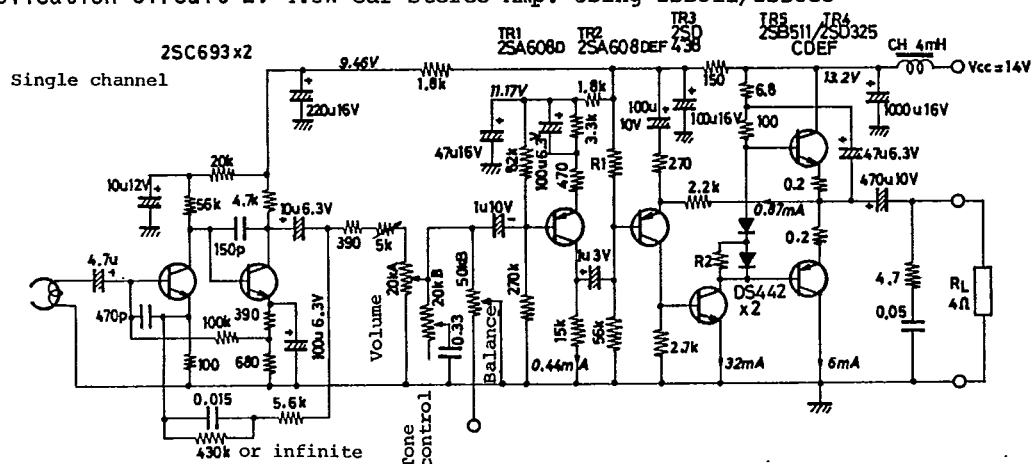


Test circuit





Application Circuit 2: 4.3W Car Stereo Amp. Using 2SB511/2SD325

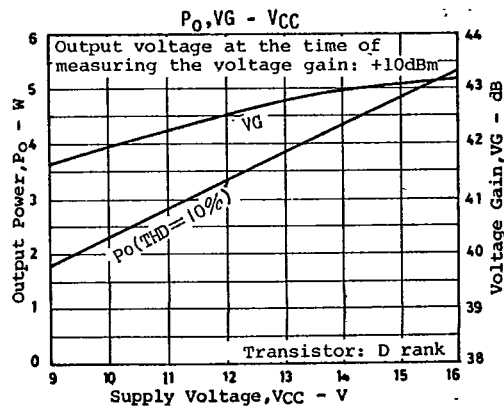
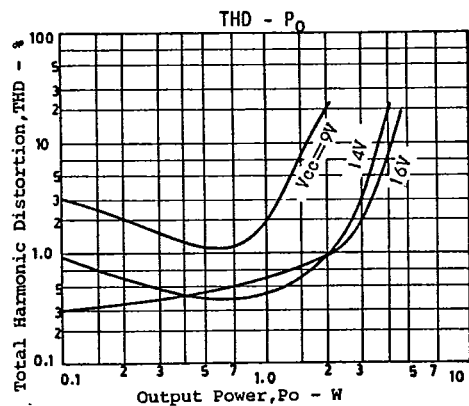
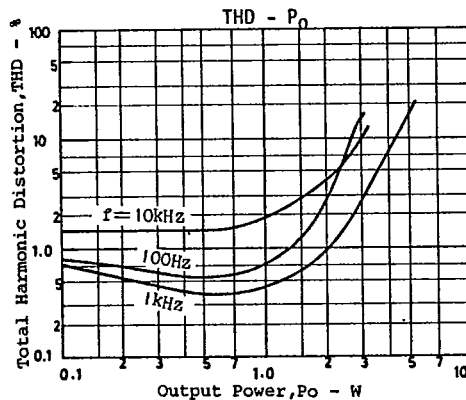
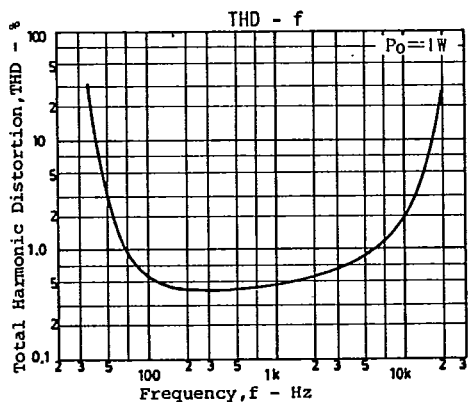
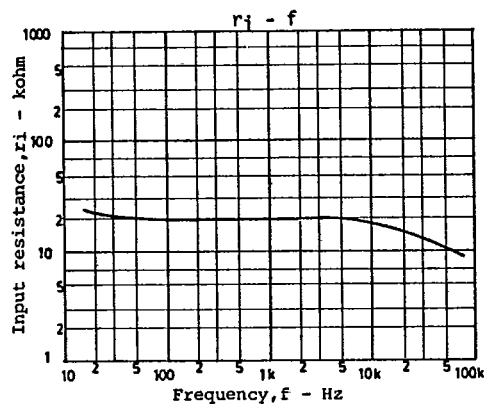
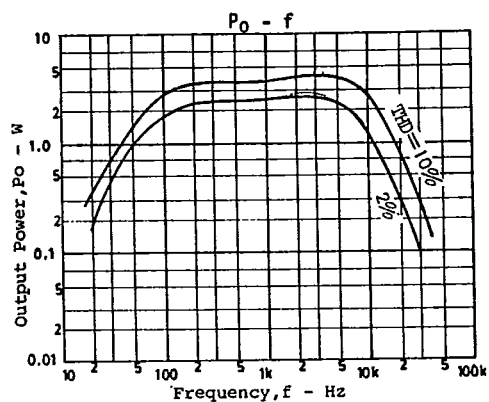
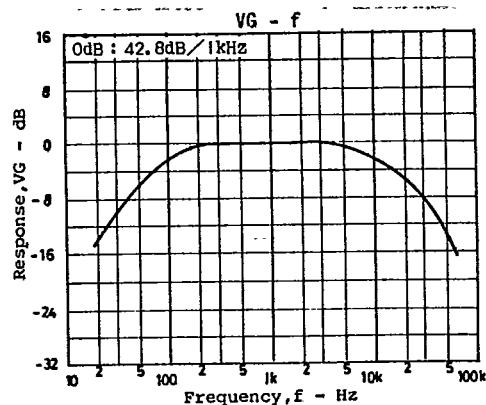
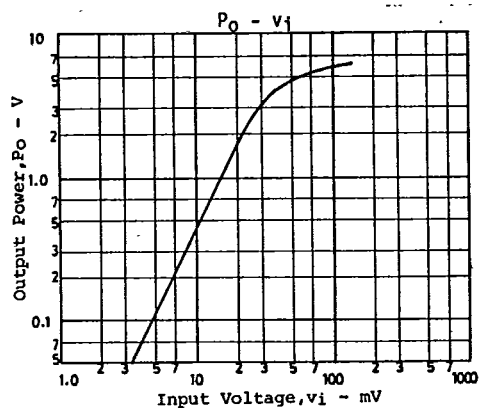


Main Characteristics at $V_{CC}=14V, R_L=4\Omega, R_g+600\Omega, f=1kHz$

Voltage Gain	VG		42.8	dB
Output Power	Po	THD=10%	3.85	W
Total Harmonic Distortion	THD	Po=1W	0.45	%
Frequency		-3dB	80 to 15k	Hz
Input Impedance	ri		20	kohm
Output Impedance	ro		0.99	ohm

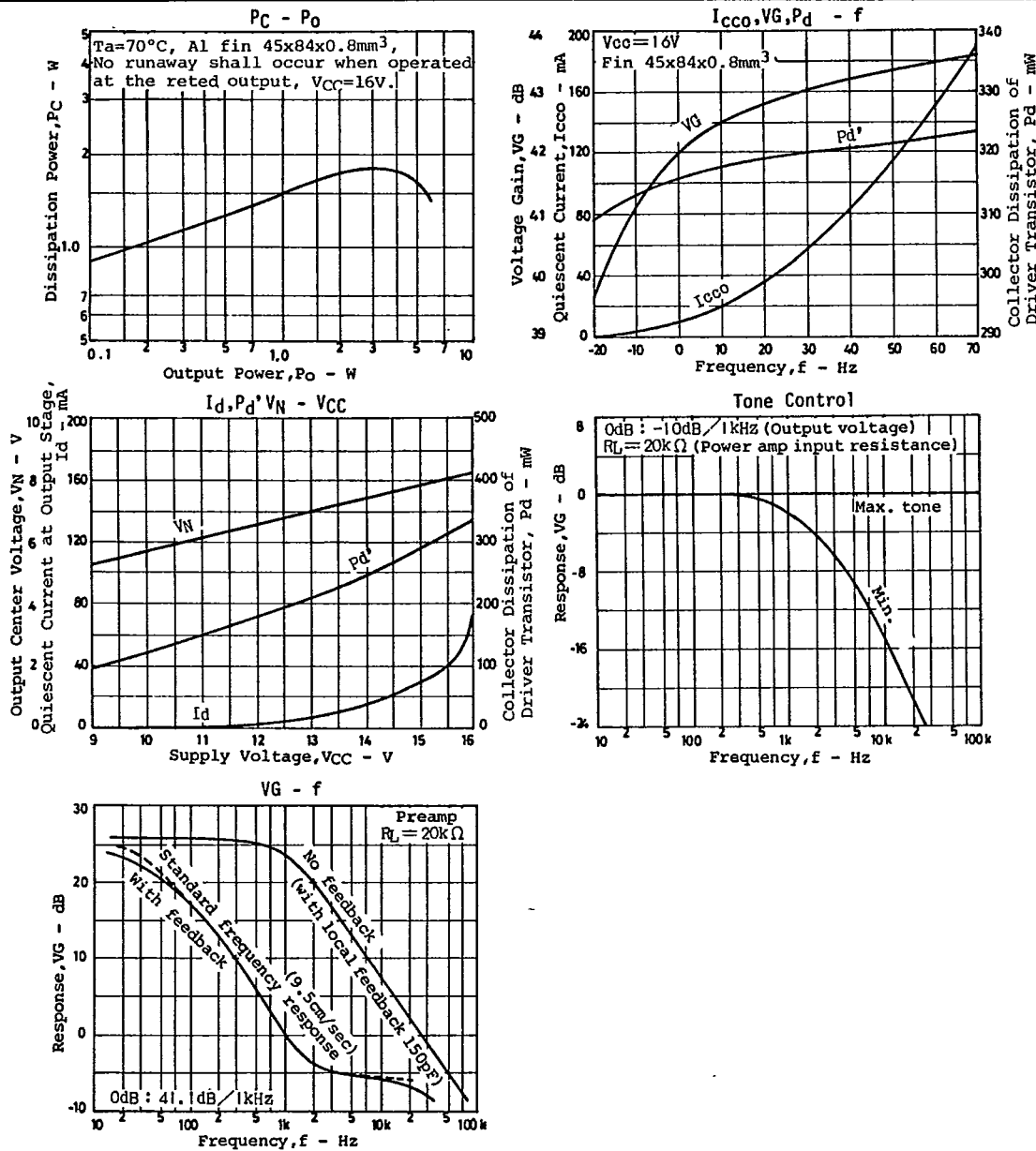
h_{FE} rank of each transistor and circuit constants corresponding to such h_{FE} rank

hfe rank					Circuit constants		Idling current (in collector of TR5)	THD 10% output	Gain
TR1	TR2	TR3	TR4	TR5	R1	R2	mA	W	dB
A608	A608	C875	D325	B511					
D	D	D	C	C	120k	13	3.5	3.3	41.8
D	F	E	C	C	100k	13	7.3	3.4	42.9
C	D	D	D	D	120k	13	6.0	3.85	42.6
D	F	E	D	D	100k	13	11.5	3.95	43.5
D	D	D	E	E	100k	13	7.2	4.1	43.0
D	F	E	E	E	82k	13	11.3	4.2	43.7
D	D	D	F	F	100k	12	7.0	4.1	43.5
D	F	E	F	F	82k	12	9.7	4.2	43.9



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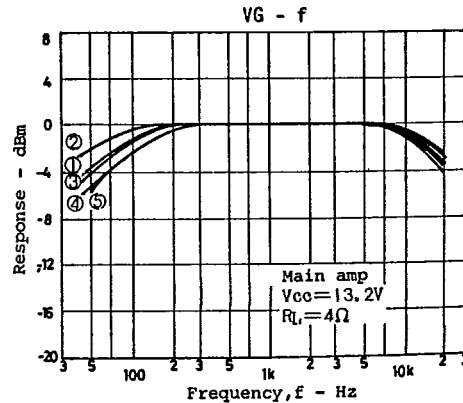
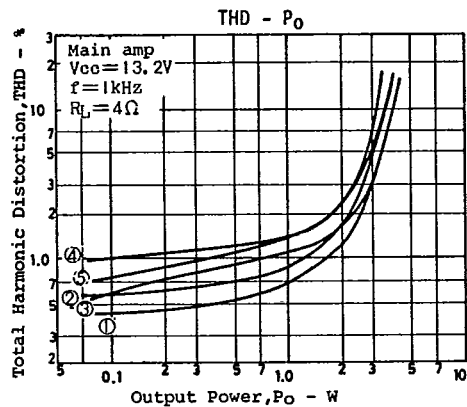
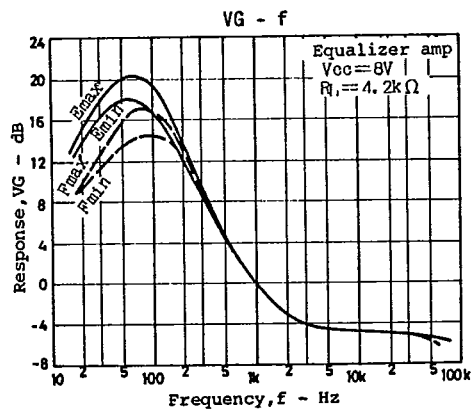
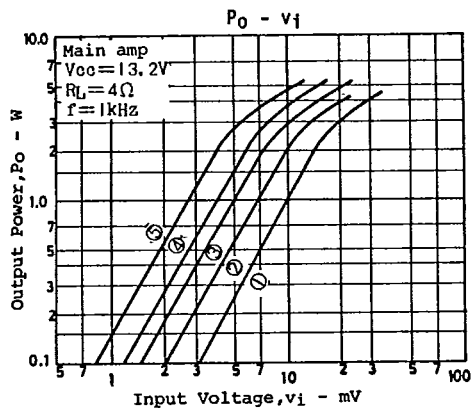
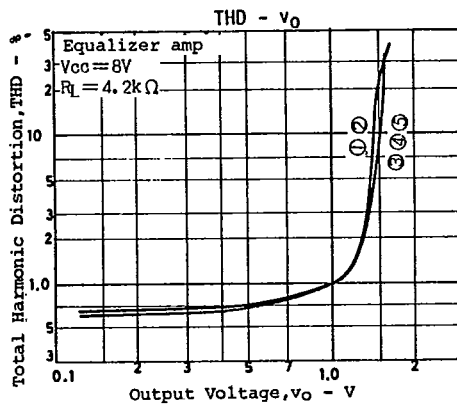
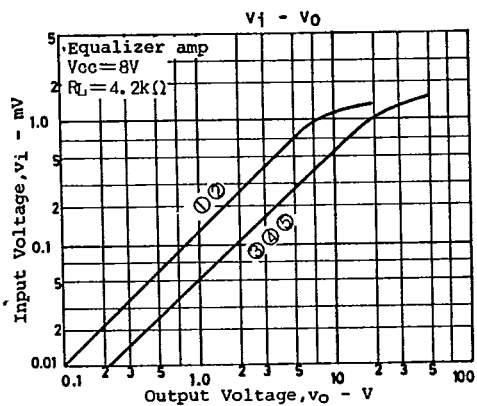
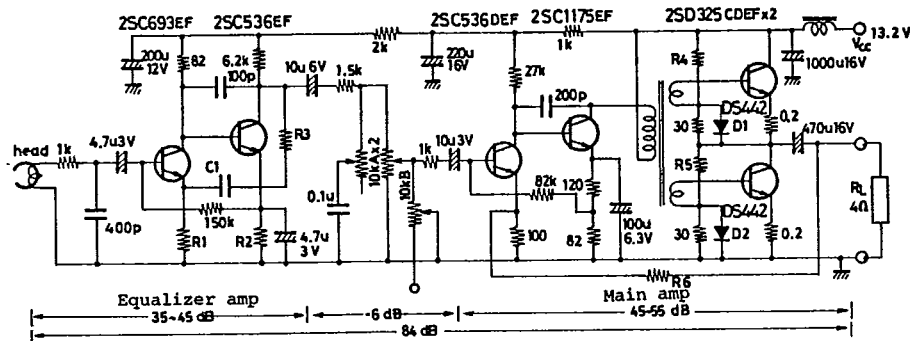


Application Circuit 3: 4W Car Stereo Pre & Main Amp Using 2SD325 x 2

hfg rank - Circuit constants - Circuit characteristics (The fraction in each column represents characteristic variations depending on the upper/lower limits of each hfg rank.)

Circuit	hfg rank					Equalizer amp									Main amp													
	C858	C537	C537	C1175	D325	R1	R2	R3	C1	V _G (NFB)	V _G (open loop)	V _G *	V _o	r ₁	R4 R5	R6	V _G (NFB)	V _G (open loop)	I _d	r ₁								
						Ω	Ω	Ω	μF	dB	dB	dB	V	Ω	Ω	Ω	dB	dB	mA	Ω								
①	F	F	E	E	C	110	750	9.1k	0.01	42.1	58.5	64.5	1.05	100k	270	30k	44.1	50.5	20	25k								
②	F	F	F	F	C					42.6	62.5	67.4	1.34	135k	270	36k	48.2	64.5	28	57k								
③	E	E	D	F	D	220	910	6.2k	0.015	33.9	53.5	60.4	0.95	100k	300	56k	47.4	56.0	25	40k								
④	E	E	D	F	E										50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8
⑤	E	E	E	F	F										50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8	50.4	67.8

* Open loop, without R_L



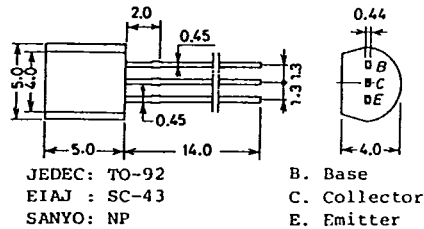
T-91-20

CASE OUTLINES AND ATTACHMENTS

- All of Sanyo Transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

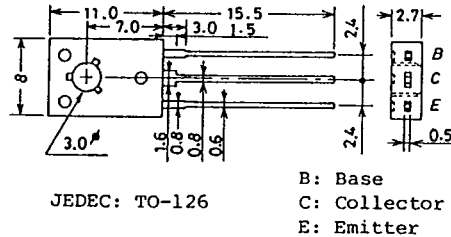
Case Outline—[2003A]

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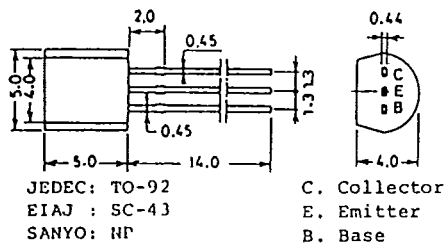
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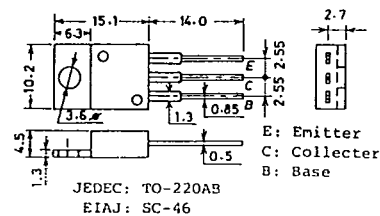
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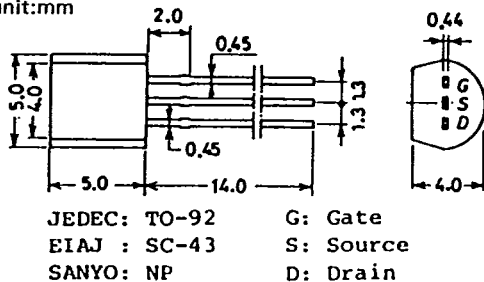
Case Outline—[2010A]

unit:mm



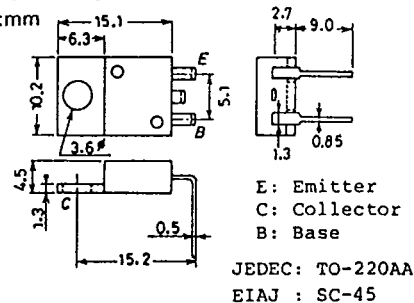
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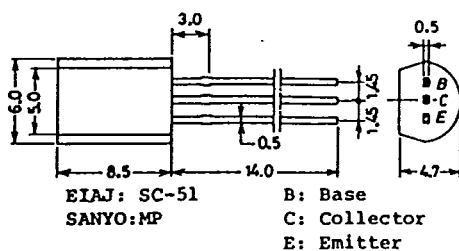
Case Outline—[2012]

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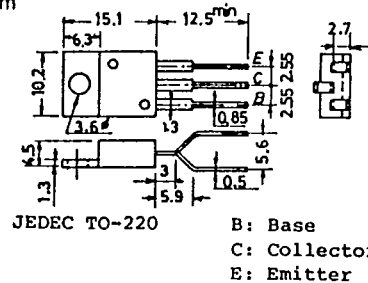
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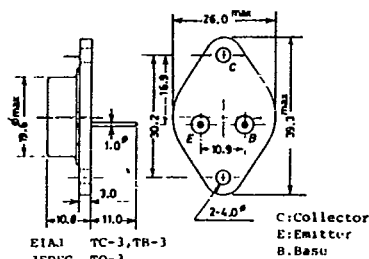


Case Outline—[2013]

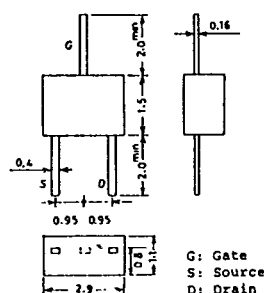
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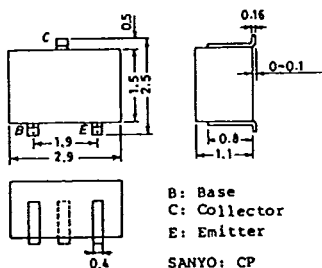


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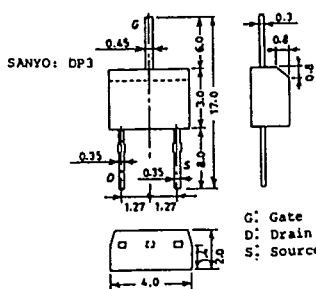


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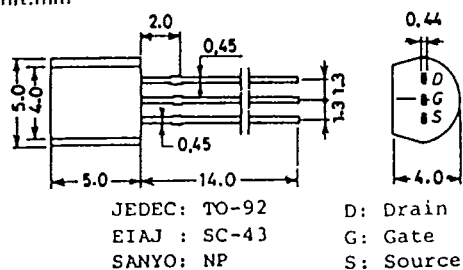
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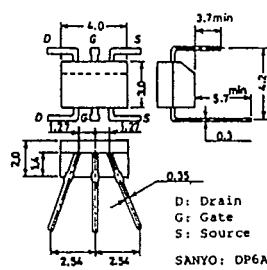
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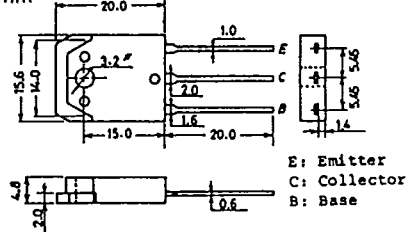
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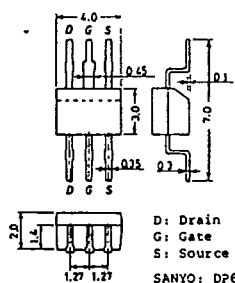
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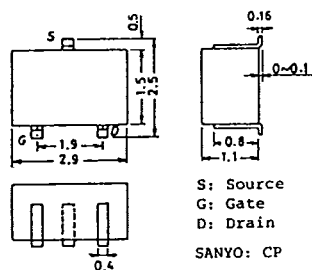
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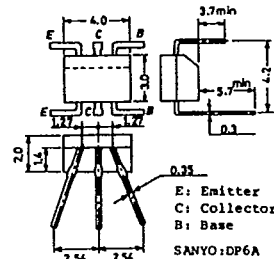
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unit:mm

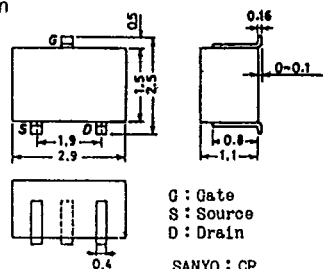


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T-91-20

unit:mm



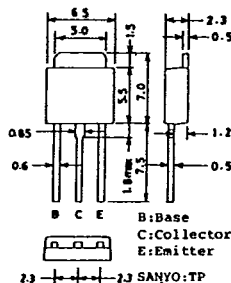
SANYO: TO126LP

G : Gate
S : Source
D : Drain

SANYO : CP

C : Collector
E : Emitter
B : Base

unit:mm

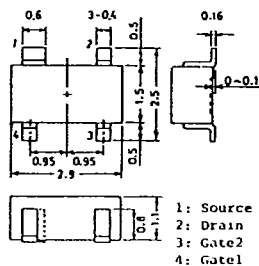


B:Base
C:Collector
E:Emitter

SANYO: SPA

1:Source
2:Drain
3:Gate

unit:mm

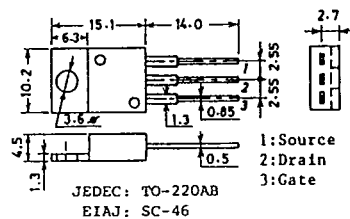


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1: Source
2: Drain
3: Gate2
4: Gate1

```

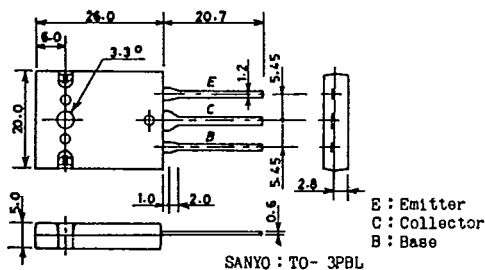
unit:mm



JEDEC: TO-220AB
EIAJ: SC-46

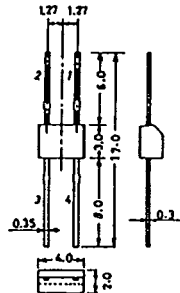
1: Drain
2: Source
3: Gate 1
4: Gate 2

Case Outline=[2040] Unit:mm



SANYO : TO- 3PBL

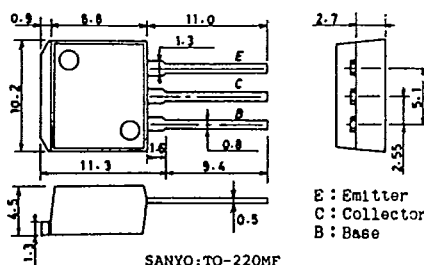
unit:mm



1: Drain
2: Source
3: Gate 1
4: Gate 2

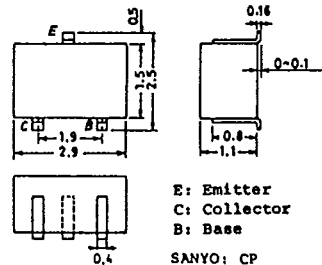
E: Emitter
C: Collector
B: Base

unit:mm



SANYO:TO-220MF

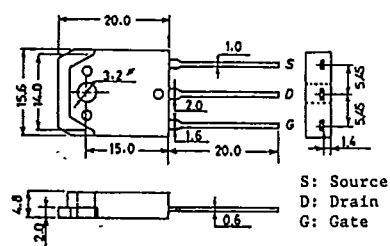
unit:mm



E: Emitter
C: Collector
B: Base

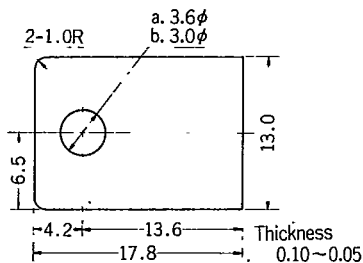
SANYO: CP

Case Outline—[2056] unit:mm



SANYO: TO3PB

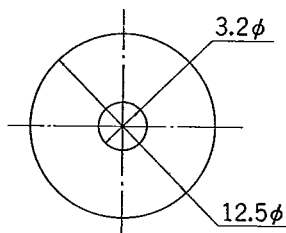
Case Outline—[0008] unit:mm

a. IS-313B
b. IS-313D

SANYO

Case Outline—[0004] unit:mm

unit:mm

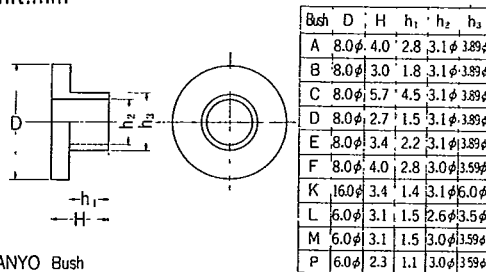


SANYO IS-126

Thickness : 0.075

Case Outline—[0009] unit:mm

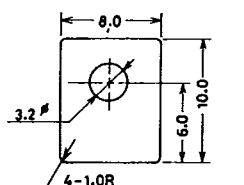
unit:mm



SANYO Bush

Case Outline—[0005] unit:mm

unit:mm

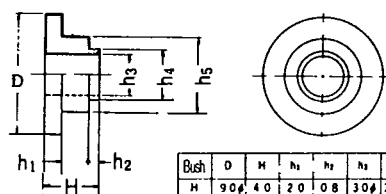


Thickness : 0.075

SANYO IS-126A Mica

Case Outline—[0010] unit:mm

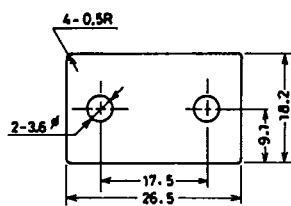
unit:mm



SANYO Bush

Case Outline—[0006] unit:mm

unit:mm

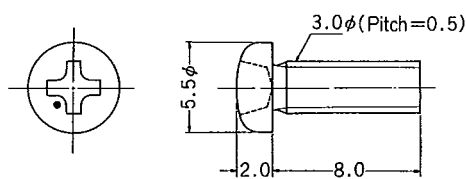


Thickness : 0.05~0.1

SANYO IS-20MA Mica

Case Outline—[0011] unit:mm

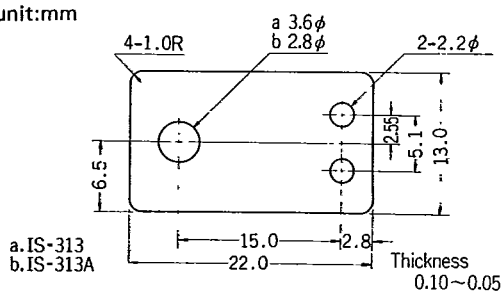
unit:mm



JIS No. B1111 M3×0.5

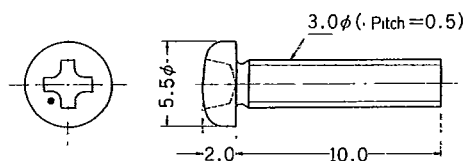
Case Outline—[0007] unit:mm

unit:mm



Case Outline—[0012] unit:mm

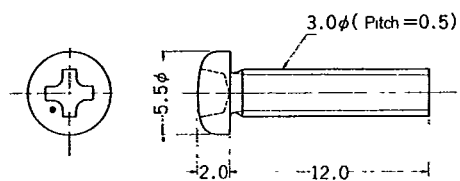
unit:mm



JIS No. B1111 M3×0.5

Case Outline—[0013]

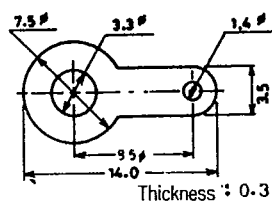
unit:mm



JIS No. B1111 M3×0.5

Case Outline—[0018]

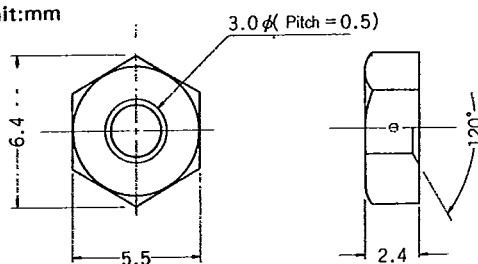
unit:mm



SANYO Lug 1.4

Case Outline—[0014]

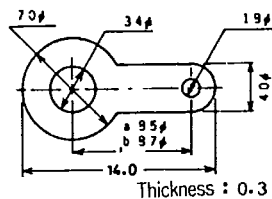
unit:mm



JIS No. B1181 M3×0.5

Case Outline—[0019]

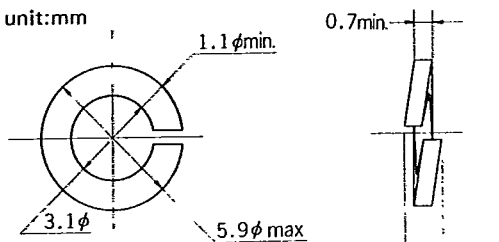
unit:mm



SANYO Lug 1.8φ

Case Outline—[0015]

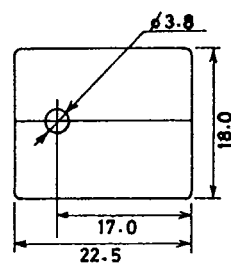
unit:mm



JIS No. B 1251 Spring washer (M3)

Case Outline—[0020]

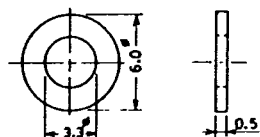
unit:mm



SANYO IS-3MP Mica

Case Outline—[0016]

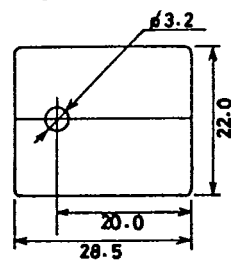
unit:mm



JIS No. B1252 Flat washer

Case Outline—[0021]

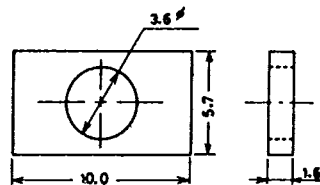
unit:mm



SANYO IS-MPC Mica

Case Outline—[0017]

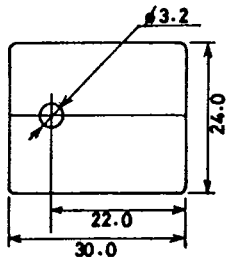
unit:mm



JIS No. G3141 Rectangular washer

Case Outline—[0022]

unit:mm



SANYO IS-3PBL Mica